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				Application Number		10/560756
				Filing Date		
				First Named Inventor		Yasuhiro Oda
				Art Unit		
Examiner Name						
Sheet	1	of	1	Attorney Docket Number		

U.S. PATENT DOCUMENT					
Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code ² (if known)		
		US			
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FOREIGN PATENT DOCUMENT							
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation ⁶
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)			
SC		JP	2005-086135	A	03-31-2005	NIPPON TELEGR&TELEPH CORP	Abstract
SC		JP	2004-214576	A	07-29-2004	NIPPON TELEGR&TELEPH CORP	Abstract
SC		JP	2003-086602	A	03-20-2004	NIPPON TELEGR&TELEPH CORP	Abstract
SC		JP	2002-270615	A	09-20-2002	AGILENT TECHNOL INC	Abstract
SC		JP	2002-270616	A	09-20-2002	AGILENT TECHNOL INC	Abstract

OTHER PRIOR ART-NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	Translation ⁶
SC		M.W.Dvorak et al., "300 GHz InP/GaAsSb/InP Double HBTs with High Current Capability and BV _{ceo} ≥ 6V", IEEE ELECTRON DEVICE LETTERS, VOL.22, NO.8, August 2001, pp361	
SC		F. Brunner et al., "Growth Monitoring of GaAsSb: C/InP Heterostructure with Reflectance Anisotropy Spectroscopy", TMS, Abstract of 12 th ICMOVPE, 2004, pp.2	
SC		Oda et al., "Suppression of hydrogen passivation in carbon-doped GaAsSb grows by MOCVD", ELSEVIER, Journal of Crystal Growth, Vol.261, 2004, pp.393	

Examiner Signature	/Sara Crane/	Date Considered	11/27/2006
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